



Reliability Report

Report Title: ADXL345 Sensor Fab Site Transfer
from TSMC to ADWL Qualification

Report Number: 20368

Revision: A

Date: 13 April 2023

Summary

This report documents the successful completion of the reliability qualification requirements for the release of the ADXL345 product in 14-LGA package with XC312A Wilmington only flow MEMS sensor. The ADXL345 is an ultralow power 3 Axis Low g accelerometer with digital output.

Substitution data was used as applicable where equivalent sensor structures were previously qualified on the Wilmington full flow or where the cap seal dimensions were the same

Die/Fab Product Characteristics

Table 1.1: Die/Fab Product Characteristics- 0.35µm CMOS

| Product Characteristics | Product(s) to be qualified |
|------------------------------|----------------------------|
| Generic/Root Part # | ADXL345 |
| Die Id | TMAF24 A_T1 / XA345D |
| Die Size (mm) | 2.25 x 1.45 |
| Wafer Fabrication Site | TSMC Fab-11 |
| Wafer Fabrication Process | 0.35µm CMOS |
| Approximate Transistor Count | 80,200 |
| Die Substrate | Si |
| Metallization / # Layers | AlCu / 3 |
| Polyimide | No |
| Passivation | undoped-oxide/SiN |

Table 1.2: Die/Fab Product Characteristics- MEMS

| Product Characteristics | Product(s) to be qualified | Product(s) used for Substitution Data | |
|---------------------------|----------------------------|---------------------------------------|-----------------|
| Generic/Root Part # | ADXL345 | ADXL313 | ADXL335 |
| Die Id | XC312A | XC365 | TC335B 1 |
| Die Size (mm) | 1.29 x 1.52 | 1.29 x 1.52 | 1.29 x 1.52 |
| Wafer Fabrication Site | ADI-Wilmington | ADI-Wilmington | TSMC Fab-2b |
| Wafer Fabrication Process | MEMS | MEMS | MEMS |
| Die Substrate | Si | Si | Si |
| Polyimide | No | No | No |
| Passivation | doped-oxide/SiN | doped-oxide/SiN | doped-oxide/SiN |

Table 1.3: Die/Fab Product Characteristics- MEMS Cap

| Product Characteristics | Product(s) to be qualified | Product(s) used for Substitution Data | |
|---------------------------|----------------------------|---------------------------------------|----------------|
| Generic/Root Part # | ADXL345 | ADXL313 | ADXL335 |
| Die Id | C345B | C313 | ADXL335CAP |
| Die Size (mm) | 1.29 x 1.52 | 1.29 x 1.52 | 1.29 x 1.52 |
| Wafer Fabrication Site | ADI-Wilmington | ADI-Wilmington | ADI-Wilmington |
| Wafer Fabrication Process | MEMS cap | MEMS Cap | MEMS Cap |
| Die Substrate | Si | Si | Si |
| Polyimide | No | No | No |
| Passivation | None | None | None |

Die/Fab Test Results
Table 2.1: Die/Fab Test Results – MEMS at ADI-Wilmington

| Test Name | Specification | Conditions | Device | Lot # | Fail/SS |
|---------------------------------------|-------------------------------|---|---------|------------|---------|
| Group D ² | MIL-STD-883, M5005 | Sub 4, Shock/Vib./Cent., Single Duration | ADXL313 | Q10157.DG1 | 0/39 |
| | | | | Q10157.DG2 | 0/39 |
| | | | | Q10157.DG3 | 0/39 |
| Mechanical Shock Powered ² | IEC 68 Part 2-27 Testgroup Ea | 10,000g, 5 Shock Pulses, 0.5ms, Single Duration | ADXL313 | Q10157.PM1 | 0/10 |
| | | | | Q10157.PM2 | 0/10 |
| | | | | Q10157.PM3 | 0/10 |
| Random Drop ² | AEC-Q100 Test G5 | 10 drops from 1.2m Single Duration | ADXL313 | Q10157.RD1 | 0/25 |
| | | | | Q10157.RD2 | 0/25 |
| | | | | Q10157.RD3 | 0/25 |
| Autoclave (AC) ¹ | JESD22-A102 | 121°C, 100%RH, 2atm, 96 Hours | ADXL335 | Q8304.1 | 0/77 |
| | | | | Q8304.2 | 0/77 |
| | | | | Q8304.4 | 0/77 |
| Temperature Cycling (TC) ¹ | JESD22-A104 | -55°C/+125°C, 1,000 Cycles | ADXL335 | Q9169.TC1 | 0/77 |
| | | | | Q9169.TC2 | 0/77 |
| | | | | Q9169.TC3 | 0/77 |
| | | | | Q9169.TC4 | 0/77 |

¹ These samples were subjected to preconditioning (per J-STD-020 Level 3) prior to the start of the stress test. Level 3 preconditioning consists of the following: Bake: 24 hrs @ 125°C, Unbiased Soak: 192 hrs @ 30°C, 60%RH, Reflow: 3 passes through an oven with a peak temperature of 260°C.

² Electrical test was performed at room temperature.

Table 3: Die/Fab Test Results – 0.35µm CMOS at TSMC Fab-11

| Test Name | Specification | Conditions | Device | Lot # | Fail/SS |
|---|--------------------------|--------------------------------------|---------|----------|---------|
| Early Life Failure Rate (ELFR) | MIL-STD-883, Method 1015 | 150°C, 48 Hours | ADXL345 | Q8378.14 | 0/320 |
| | | | | Q8378.15 | 0/320 |
| | | | | Q8378.16 | 0/160 |
| | | | | Q8378.19 | 0/160 |
| | | | | Q8378.20 | 0/320 |
| | | | | Q8378.21 | 0/320 |
| | | | | Q8378.22 | 0/160 |
| Highly Accelerated Temperature and Humidity Stress Test (HAST) ¹ | JESD22-A110 | 130°C, 85%RH, 2atm, Biased, 96 Hours | ADXL345 | Q9681.10 | 0/77 |
| | | | | Q9681.11 | 0/77 |
| | | | | Q9681.12 | 0/77 |
| High Temperature Storage Life (HTSL) | JESD22-A103 | 150°C, 1,000 Hours | ADXL345 | Q9681.19 | 0/77 |
| | | | | Q9681.20 | 0/77 |
| | | | | Q9681.21 | 0/77 |
| | | | | Q9681.31 | 0/77 |
| | | | | Q9681.32 | 0/77 |
| High Temperature Operating Life (HTOL) ¹ | JESD22-A108 | Ta=150C, Biased, 500 Hours | ADXL345 | Q9681.1 | 0/77 |
| | | | | Q9681.2 | 0/77 |
| | | | | Q9681.3 | 0/77 |

¹ These samples were subjected to preconditioning (per J-STD-020 Level 3) prior to the start of the stress test. Level 3 preconditioning consists of the following: Bake: 24 hrs @ 125°C, Unbiased Soak: 192 hrs @ 30°C, 60%RH, Reflow: 3 passes through an oven with a peak temperature of 260°C.

Package/Assembly Product Characteristics

Table 4: Package/Assembly Product Characteristics - 14-LGA at AMKOR (AP3)

| Product Characteristics | Product(s) to be qualified |
|---------------------------------------|----------------------------|
| Generic/Root Part # | ADXL345 |
| Package | 14-LGA |
| Body Size (mm) | 3.00 x 5.00 x 0.95 |
| Assembly Location | AMKOR (AP3) |
| MSL/Peak Reflow Temperature(°C) | 3 / 260 |
| Mold Compound | Sumitomo G770 |
| Die Attach/Underfill/TIM | Ablestik 2300 / N/A |
| Leadframe Material | BT Resin / HL-832NX-A |
| Lead Finish | Au |
| Wire Bond Material/Diameter (mils) | Tanaka GPG 2N Gold / 1.00 |

Package/Assembly Test Results
Table 5: Package/Assembly Test Results - 14-LGA at AMKOR (AP3)

| Test Name | Specification | Conditions | Device | Lot # | Fail/SS |
|---|--------------------|---|---------|----------|---------|
| Unbiased HAST (UHST) ¹ | JESD22-A118 | 130°C, 85%RH, 2atm, 96 Hours | ADXL345 | Q9681.13 | 0/77 |
| | | | | Q9681.14 | 0/77 |
| | | | | Q9681.15 | 0/77 |
| Group D | MIL-STD-883, M5005 | Sub 4, Shock/Vib./Cent./Seal, Single Duration | ADXL345 | Q9327.13 | 0/20 |
| | | | | Q9327.14 | 0/20 |
| | | | | Q9327.15 | 0/20 |
| Random Drop | CAM0091 | 10 drops from 1.2m, Single Duration | ADXL345 | Q9681.25 | 0/35 |
| | | | | Q9681.26 | 0/35 |
| | | | | Q9681.27 | 0/35 |
| Highly Accelerated Temperature and Humidity Stress Test (HAST) ¹ | JESD22-A110 | 130°C, 85%RH, 2atm, Biased, 96 Hours | ADXL345 | Q9681.10 | 0/77 |
| | | | | Q9681.11 | 0/77 |
| | | | | Q9681.12 | 0/77 |
| Temperature Cycling (TC) ¹ | JESD22-A104 | -65°C/+150°C, 500 Cycles | ADXL345 | Q9681.7 | 0/77 |
| | | | | Q9681.8 | 0/77 |
| | | | | Q9681.9 | 0/77 |
| Temperature Cycling (TC) ¹ | JESD22-A104 | -65°C/+150°C, 1000 Cycles, 1 Cycle per Hour | ADXL345 | Q9681.4 | 0/77 |
| | | | | Q9681.5 | 0/77 |
| | | | | Q9681.6 | 0/77 |
| Solder Heat Resistance (SHR) ¹ | ADI-0049 | MSL-3 | ADXL345 | Q9327.16 | 0/11 |
| | | | | Q9327.17 | 0/11 |
| | | | | Q9327.23 | 0/11 |
| High Temperature Storage Life (HTSL) | JESD22-A103 | 150°C, 1,000 Hours | ADXL345 | Q9681.19 | 0/77 |
| | | | | Q9681.20 | 0/77 |
| | | | | Q9681.21 | 0/77 |
| | | | | Q9681.31 | 0/77 |
| | | | | Q9681.32 | 0/77 |

¹ These samples were subjected to preconditioning (per J-STD-020 Level 3) prior to the start of the stress test. Level 3 preconditioning consists of the following: Bake: 24 hrs @ 125°C, Unbiased Soak: 192 hrs @ 30°C, 60%RH, Reflow: 3 passes through an oven with a peak temperature of 260°C.

ESD Test Results

The results of Human Body Model (HBM), Machine Model (MM), and Field-Induced Charged Device Model (FICDM) ESD testing are summarized in Table 6. ADI measures ESD results using stringent test procedures based on the specifications listed. Any comparison with another supplier's results should ensure that the same ESD test procedures have been used. For further details, please see the EOS/ESD chapter of the ADI Reliability Handbook (available via the 'Quality and Reliability' link on [Analog Devices' web site](#)).

Table 6: ADXL345 ESD Test Results

| ESD Model | Package | ESD Test Spec | RC Network | Highest Pass Level | First Fail Level | Class |
|-----------|---------|------------------------|--------------|--------------------|------------------|-------|
| FICDM | 14-LGA | ANSI/ESD STM5.3.1-1999 | 1Ω, Cpkg | ±1500V | NA | NA |
| | | JESD22-C101 | | ±1500V | NA | IV |
| HBM | 14-LGA | ANSI/ESD STM5.1-2007 | 1.5kΩ, 100pF | ±2000V | NA | NA |
| | | ESDA/JEDEC JS-001-2011 | | ±2000V | NA | 2 |
| MM | 14-LGA | ANSI/ESD STM5.2-1999 | 0Ω, 200pF | ±200V | NA | M3 |
| | | JESD22-A115 | | ±200V | NA | NA |

Approvals

Reliability Engineer: Michael Walornyj

Additional Information

Data sheets and other additional information are available on [Analog Devices' web site](#)